



CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

General Purpose Transistor

VOLTAGE 25 Volts CURRENT 200 mAmpere

CHT4126WPT

APPLICATION

- * AF input stages and driver applicationon equipment.
- * Other general purpose applications.

FEATURE

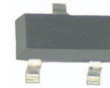
- * Small surface mounting type. (SC-70/SOT-323)
- * High current gain.
- * Suitable for high packing density.
- * Low collector-emitter saturation.
- * High saturation current capability.

CONSTRUCTION

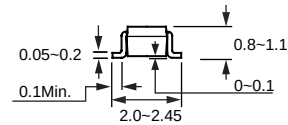
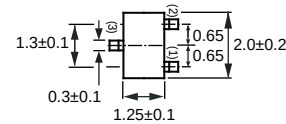
- * PNP Silicon Transistor

MARKING

- * DW



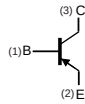
SC-70/SOT-323



Dimensions in millimeters

SC-70/SOT-323

CIRCUIT



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	—	-25	V
V _{CEO}	collector-emitter voltage	open base	—	-25	V
V _{EBO}	emitter-base voltage	open collector	—	-4	V
I _C	collector current (DC)		—	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 2	—	300	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		—	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

2004-8

2. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC CURVES (CHT4126WPT)

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specided.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = -10\mu\text{A}$; $I_E = 0\text{A}$	-25	—	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = -1\text{mA}$; $I_B = 0\text{A}$	-25	—	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = -10\mu\text{A}$; $I_C = 0\text{A}$	-4	—	V
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -20\text{ V}$	—	-50	nA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = -3\text{ V}$	—	-50	nA
h_{FE}	DC current gain	$I_C = -50\text{ mA}$; $V_{CE} = -1\text{V}$; note 3	60	—	
h_{FE}	DC current gain	$I_C = -2\text{ mA}$; $V_{CE} = -1\text{V}$	120	360	
V_{CEsat}	collector-emitter saturation	$I_C = -50\text{ mA}$; $I_B = -5\text{ mA}$	—	-400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -50\text{ mA}$; $I_B = -5\text{ mA}$	—	-950	mV
C_{obo}	output capacitance	$I_E = I_e = 0$; $V_{CB} = -5\text{ V}$; $f = 1\text{ MHz}$	—	4.5	pF
C_{ibo}	input capacitance	$I_E = I_e = 0$; $V_{CB} = -5\text{ V}$; $f = 1\text{ MHz}$	—	10	pF
f_T	transition frequency	$I_C = -10\text{mA}$; $V_{CE} = -20\text{ V}$; $f = 100\text{ MHz}$	250	—	MHz

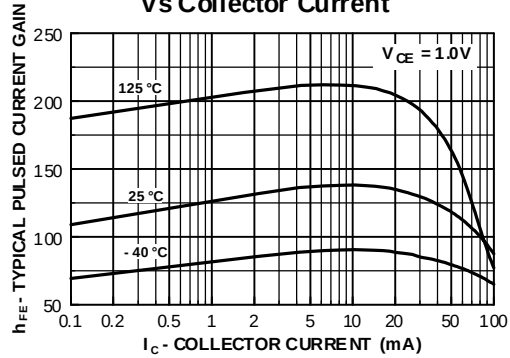
Note

3. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

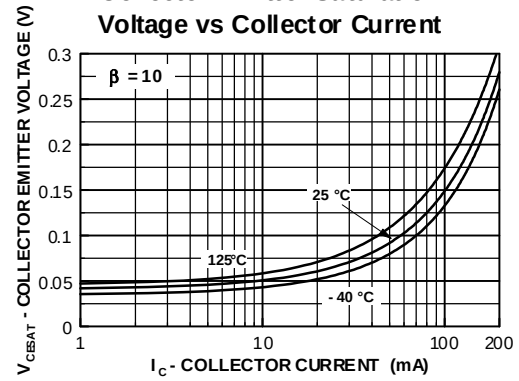
RATING CHARACTERISTIC CURVES (CHT4126WPT)

Typical Characteristics

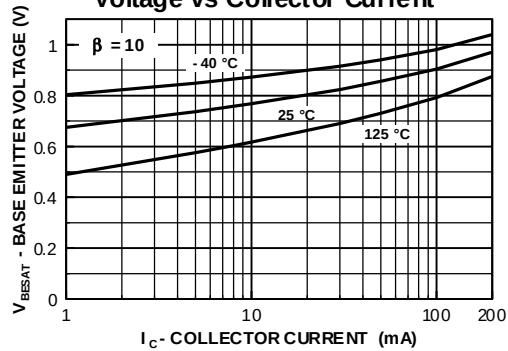
Typical Pulsed Current Gain
vs Collector Current



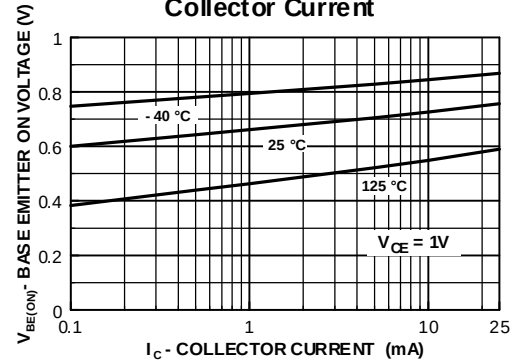
Collector-Emitter Saturation
Voltage vs Collector Current



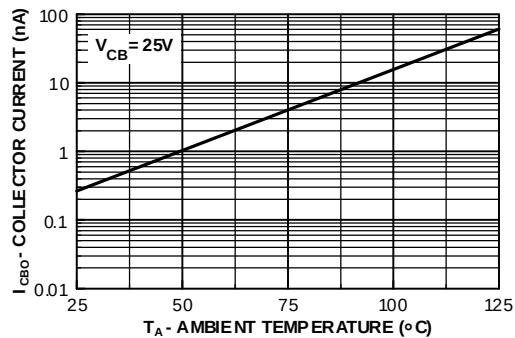
Base-Emitter Saturation
Voltage vs Collector Current



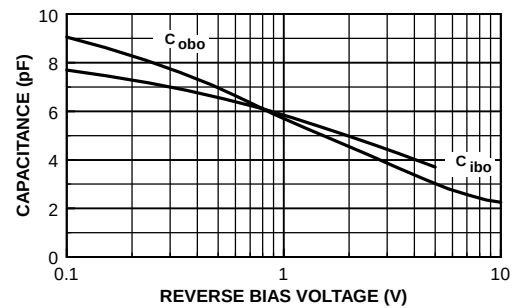
Base Emitter ON Voltage vs
Collector Current



Collector-Cutoff Current
vs Ambient Temperature



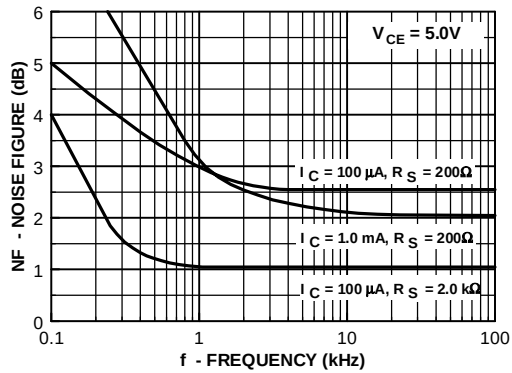
Common-Base Open Circuit
Input and Output Capacitance
vs Reverse Bias Voltage



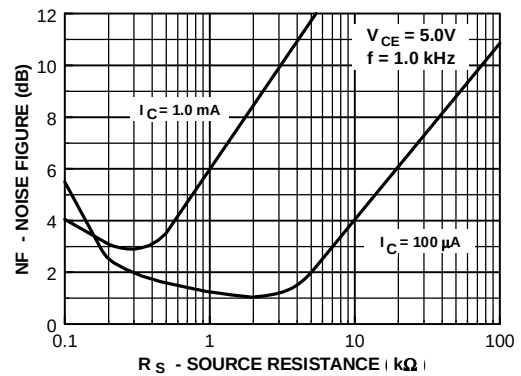
RATING CHARACTERISTIC CURVES (CHT4126WPT)

Typical Characteristics

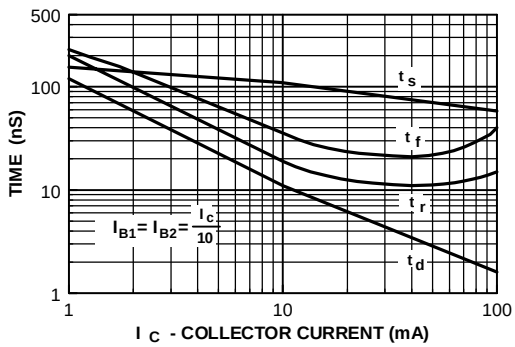
Noise Figure vs Frequency



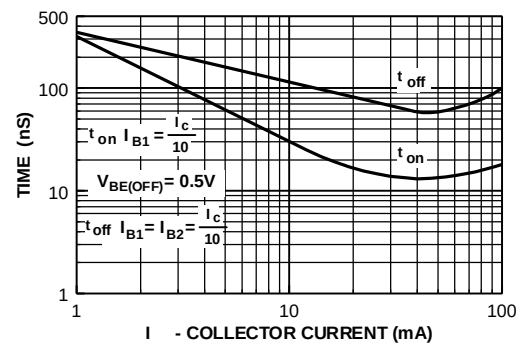
Noise Figure vs Source Resistance



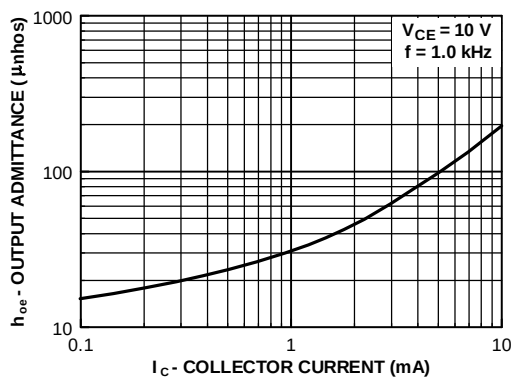
Switching Times vs Collector Current



Turn On and Turn Off Times vs Collector Current



Output Admittance



Current Gain

